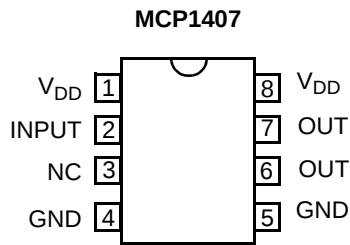
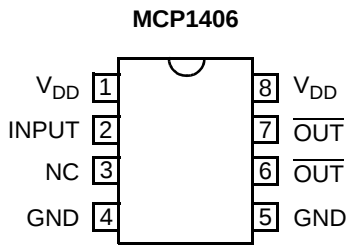


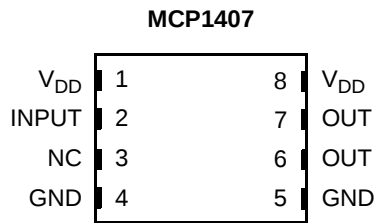
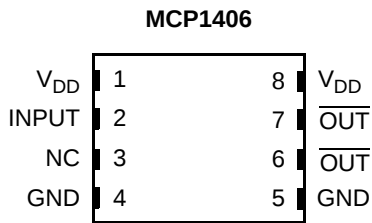
MCP1406/07

Package Types

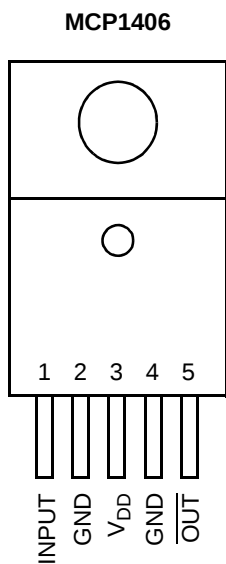
8-Pin PDIP/SOIC



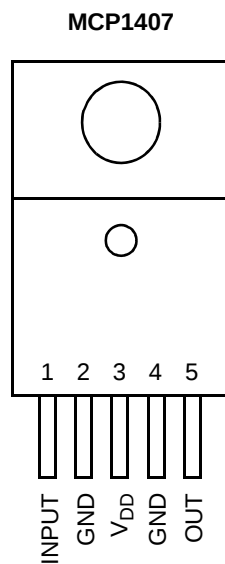
8-Pin 6x5 DFN



5-Pin TO-220

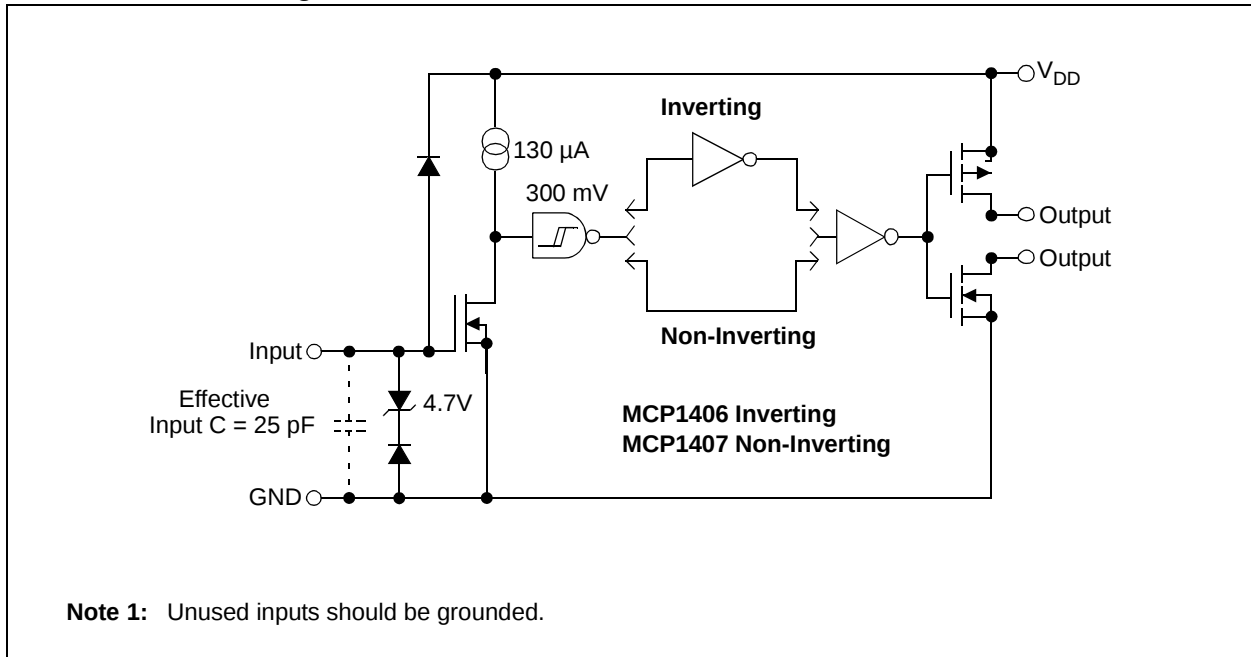


Tab is common to V_{DD}



- Note 1:** Duplicate pins must both be connected for proper operation.
- 2:** Exposed pad of the DFN package is electrically isolated.

Functional Block Diagram⁽¹⁾



MCP1406/07

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

Supply Voltage+20V
 Input Voltage ($V_{DD} + 0.3V$) to (GND – 5V)
 Input Current ($V_{IN} > V_{DD}$)50 mA

† **Notice:** Stresses above those listed under “Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise indicated, $T_A = +25^\circ C$, with $4.5V \leq V_{DD} \leq 18V$.						
Parameters	Sym	Min	Typ	Max	Units	Conditions
Input						
Logic '1', High Input Voltage	V_{IH}	2.4	1.8	—	V	
Logic '0', Low Input Voltage	V_{IL}	—	1.3	0.8	V	
Input Current	I_{IN}	–10	—	10	μA	$0V \leq V_{IN} \leq V_{DD}$
Input Voltage	V_{IN}	–5	—	$V_{DD} + 0.3$	V	
Output						
High Output Voltage	V_{OH}	$V_{DD} - 0.025$	—	—	V	DC Test
Low Output Voltage	V_{OL}	—	—	0.025	V	DC Test
Output Resistance, High	R_{OH}	—	2.1	2.8	Ω	$I_{OUT} = 10\text{ mA}$, $V_{DD} = 18V$
Output Resistance, Low	R_{OL}	—	1.5	2.5	Ω	$I_{OUT} = 10\text{ mA}$, $V_{DD} = 18V$
Peak Output Current	I_{PK}	—	6	—	A	$V_{DD} = 18V$ (Note 2)
Continuous Output Current	I_{DC}	1.3			A	Note 2, Note 3
Latch-Up Protection Withstand Reverse Current	I_{REV}	—	1.5	—	A	Duty cycle $\leq 2\%$, $t \leq 300\text{ }\mu\text{sec}$.
Switching Time (Note 1)						
Rise Time	t_R	—	20	30	ns	Figure 4-1, Figure 4-2 $C_L = 2500\text{ pF}$
Fall Time	t_F	—	20	30	ns	Figure 4-1, Figure 4-2 $C_L = 2500\text{ pF}$
Delay Time	t_{D1}	—	40	55	ns	Figure 4-1, Figure 4-2
Delay Time	t_{D2}	—	40	55	ns	Figure 4-1, Figure 4-2
Power Supply						
Supply Voltage	V_{DD}	4.5	—	18.0	V	
Power Supply Current	I_S	—	130	250	μA	$V_{IN} = 3V$
	I_S	—	35	100	μA	$V_{IN} = 0V$

- Note 1:** Switching times ensured by design.
2: Tested during characterization, not production tested.
3: Valid for AT and MF packages only. $T_A = +25^\circ C$

DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise indicated, operating temperature range with $4.5V \leq V_{DD} \leq 18V$.						
Parameters	Sym	Min	Typ	Max	Units	Conditions
Input						
Logic '1', High Input Voltage	V_{IH}	2.4	—	—	V	
Logic '0', Low Input Voltage	V_{IL}	—	—	0.8	V	
Input Current	I_{IN}	-10	—	+10	μA	$0V \leq V_{IN} \leq V_{DD}$
Input Voltage	V_{IN}	-5	—	$V_{DD}+0.3$	V	
Output						
High Output Voltage	V_{OH}	$V_{DD} - 0.025$	—	—	V	DC TEST
Low Output Voltage	V_{OL}	—	—	0.025	V	DC TEST
Output Resistance, High	R_{OH}	—	3.0	5.0	Ω	$I_{OUT} = 10 \text{ mA}, V_{DD} = 18V$
Output Resistance, Low	R_{OL}	—	2.3	5.0	Ω	$I_{OUT} = 10 \text{ mA}, V_{DD} = 18V$
Switching Time (Note 1)						
Rise Time	t_R	—	25	40	ns	Figure 4-1, Figure 4-2 $C_L = 2500 \text{ pF}$
Fall Time	t_F	—	25	40	ns	Figure 4-1, Figure 4-2 $C_L = 2500 \text{ pF}$
Delay Time	t_{D1}	—	50	65	ns	Figure 4-1, Figure 4-2
Delay Time	t_{D2}	—	50	65	ns	Figure 4-1, Figure 4-2
Power Supply						
Supply Voltage	V_{DD}	4.5	—	18.0	V	
Power Supply Current	I_S	—	200	500	μA	$V_{IN} = 3V$
		—	50	150		$V_{IN} = 0V$

Note 1: Switching times ensured by design.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, all parameters apply with $4.5V \leq V_{DD} \leq 18V$.						
Parameters	Sym	Min	Typ	Max	Units	Conditions
Temperature Ranges						
Specified Temperature Range	T_A	-40	—	+125	$^{\circ}C$	
Maximum Junction Temperature	T_J	—	—	+150	$^{\circ}C$	
Storage Temperature Range	T_A	-65	—	+150	$^{\circ}C$	
Package Thermal Resistances						
Thermal Resistance, 8L-6x5 DFN	θ_{JA}	—	33.2	—	$^{\circ}C/W$	Typical four-layer board with vias to ground plane
Thermal Resistance, 8L-PDIP	θ_{JA}	—	125	—	$^{\circ}C/W$	
Thermal Resistance, 8L-SOIC	θ_{JA}	—	155	—	$^{\circ}C/W$	
Thermal Resistance, 5L-TO-220	θ_{JA}	—	71	—	$^{\circ}C/W$	

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^\circ\text{C}$ with $4.5\text{V} \leq V_{DD} \leq 18\text{V}$.

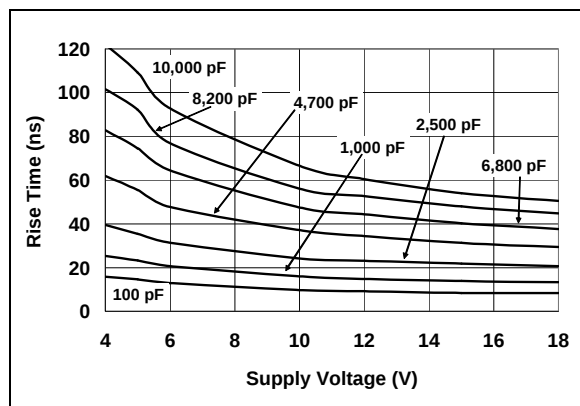


FIGURE 2-1: Rise Time vs. Supply Voltage.

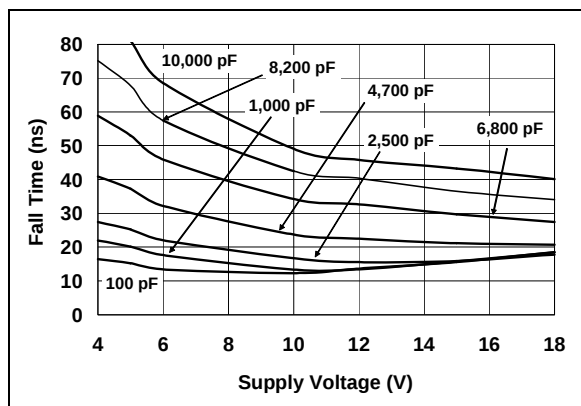


FIGURE 2-4: Fall Time vs. Supply Voltage.

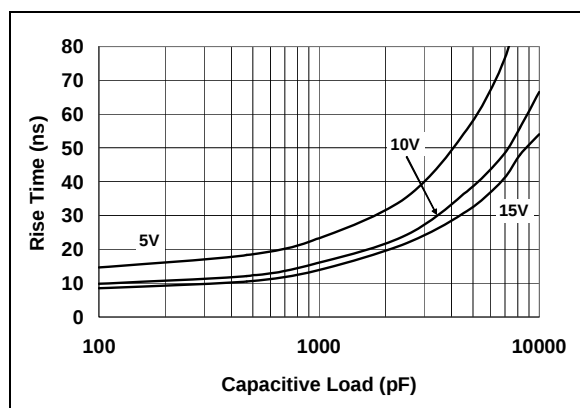


FIGURE 2-2: Rise Time vs. Capacitive Load.

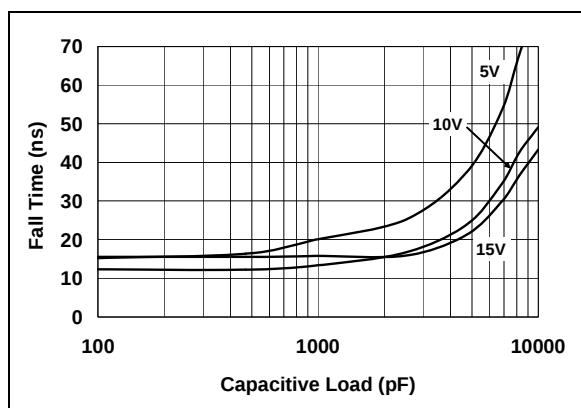


FIGURE 2-5: Fall Time vs. Capacitive Load.

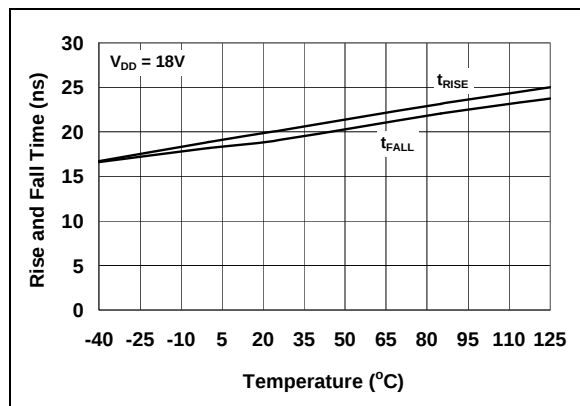


FIGURE 2-3: Rise and Fall Times vs. Temperature.

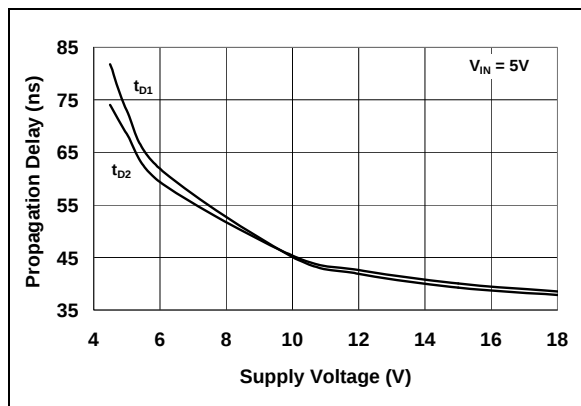


FIGURE 2-6: Propagation Delay vs. Supply Voltage.

Note: Unless otherwise indicated, $T_A = +25^\circ\text{C}$ with $4.5\text{V} \leq V_{DD} \leq 18\text{V}$.

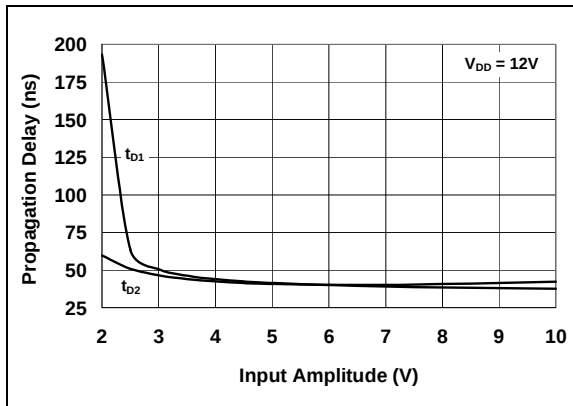


FIGURE 2-7: Propagation Delay Time vs. Input Amplitude.

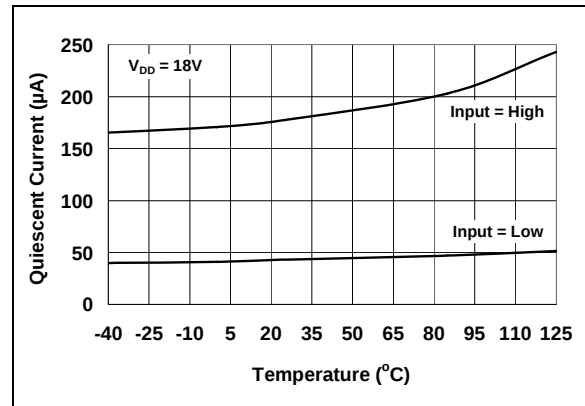


FIGURE 2-10: Quiescent Current vs. Temperature.

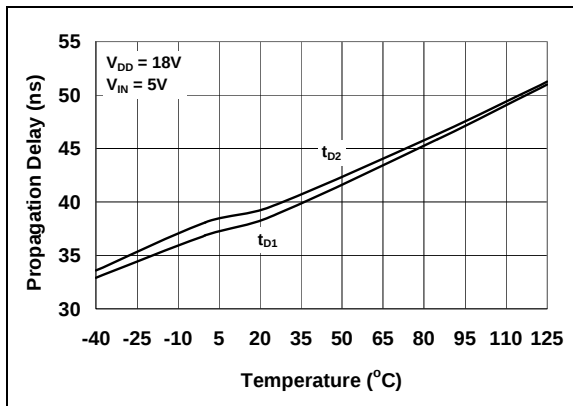


FIGURE 2-8: Propagation Delay Time vs. Temperature.

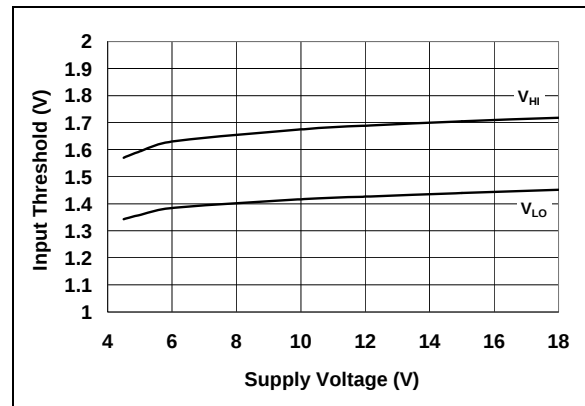


FIGURE 2-11: Input Threshold vs. Supply Voltage.

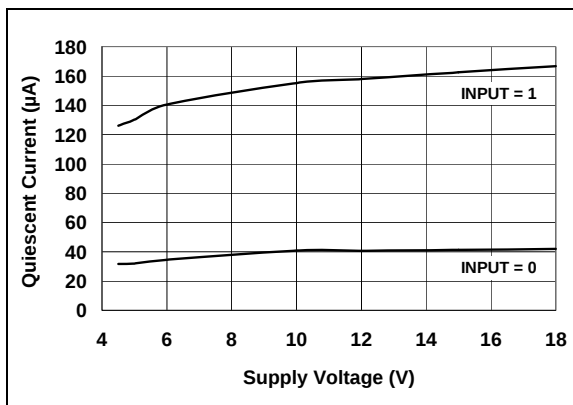


FIGURE 2-9: Quiescent Current vs. Supply Voltage.

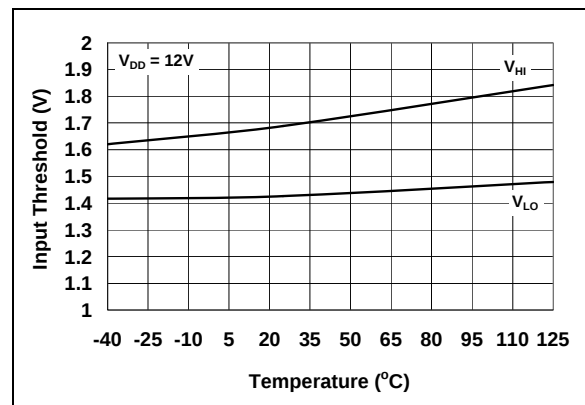


FIGURE 2-12: Input Threshold vs. Temperature.

MCP1406/07

Note: Unless otherwise indicated, $T_A = +25^\circ\text{C}$ with $4.5\text{V} \leq V_{DD} \leq 18\text{V}$.

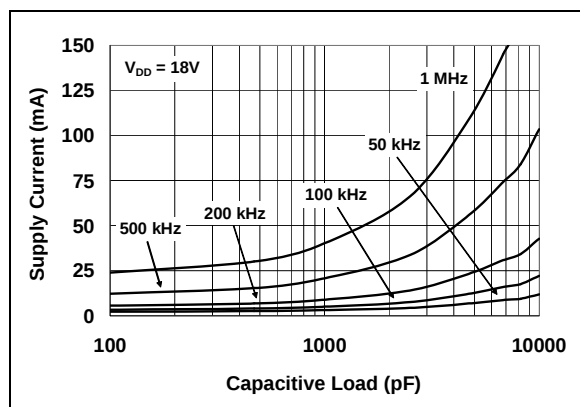


FIGURE 2-13: Supply Current vs. Capacitive Load.

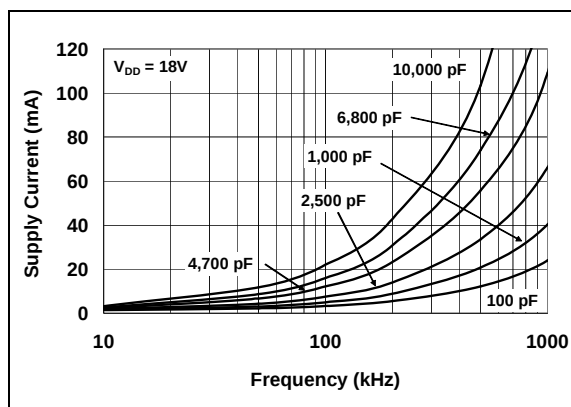


FIGURE 2-16: Supply Current vs. Frequency.

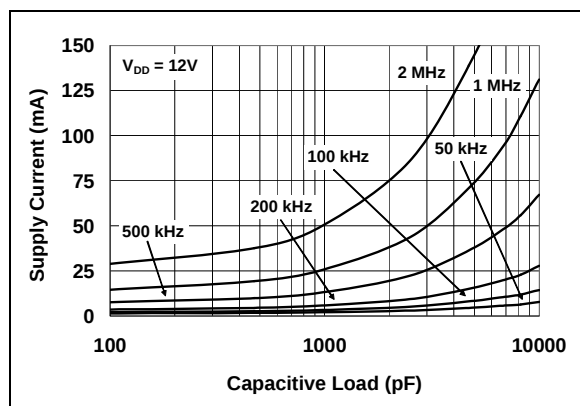


FIGURE 2-14: Supply Current vs. Capacitive Load.

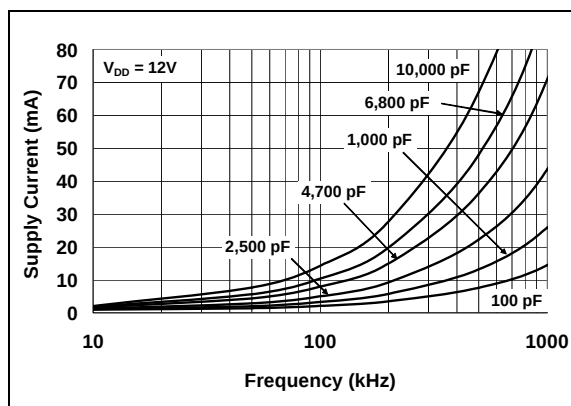


FIGURE 2-17: Supply Current vs. Frequency.

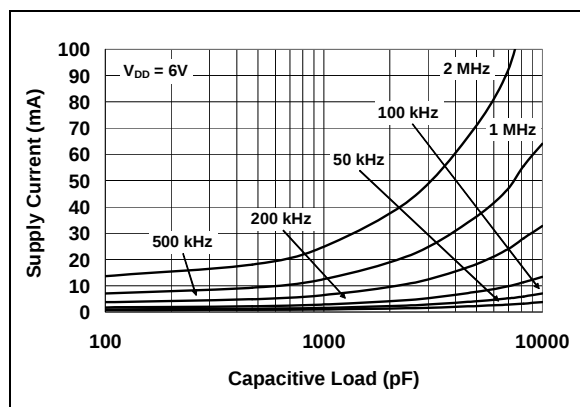


FIGURE 2-15: Supply Current vs. Capacitive Load.

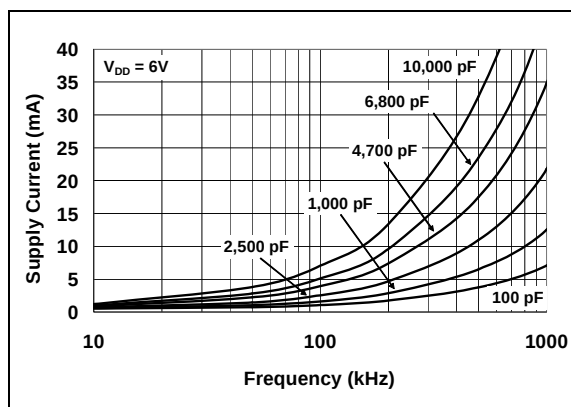


FIGURE 2-18: Supply Current vs. Frequency.

Note: Unless otherwise indicated, $T_A = +25^{\circ}\text{C}$ with $4.5\text{V} \leq V_{DD} \leq 18\text{V}$.

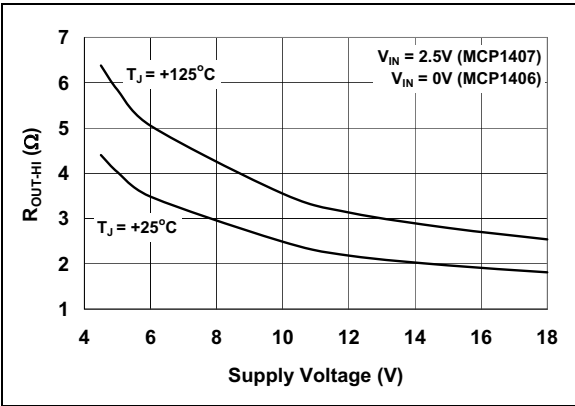


FIGURE 2-19: Output Resistance (Output High) vs. Supply Voltage.

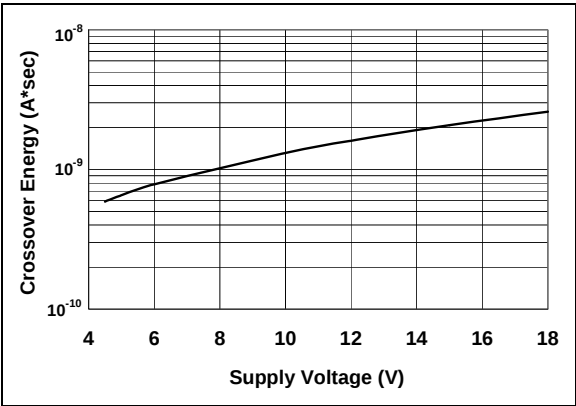


FIGURE 2-21: Crossover Energy vs. Supply Voltage.

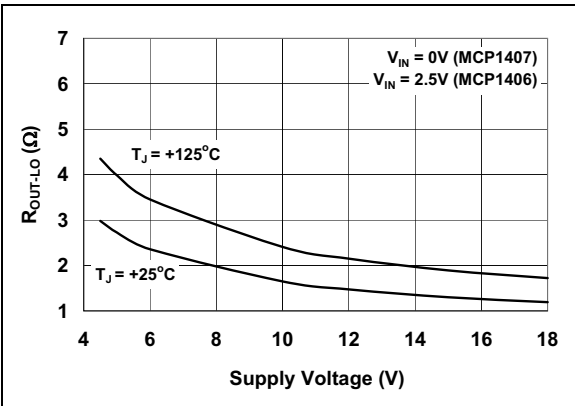


FIGURE 2-20: Output Resistance (Output Low) vs. Supply Voltage.

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3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in [Table 3-1](#).

TABLE 3-1: PIN FUNCTION TABLE⁽¹⁾

8-Pin PDIP, SOIC	8-Pin DFN	5-Pin TO-220	Symbol	Description
1	1	—	V_{DD}	Supply Input
2	2	1	INPUT	Control Input
3	3	—	NC	No Connection
4	4	2	GND	Ground
5	5	4	GND	Ground
6	6	5	OUTPUT	CMOS Push-Pull Output
7	7	—	OUTPUT	CMOS Push-Pull Output
8	8	3	V_{DD}	Supply Input
—	PAD	—	NC	Exposed Metal Pad
—	—	TAB	V_{DD}	Metal Tab at V_{DD} Potential

Note 1: Duplicate pins must be connected for proper operation.

3.1 Supply Input (V_{DD})

V_{DD} is the bias supply input for the MOSFET driver and has a voltage range of 4.5V to 18V. This input must be decoupled to ground with local capacitors. The bypass capacitors provide a localized low-impedance path for the peak currents that are to be provided to the load.

3.2 Control Input (INPUT)

The MOSFET driver input is a high-impedance, TTL/CMOS-compatible input. The input also has hysteresis between the high and low input levels, allowing them to be driven from slow rising and falling signals, and to provide noise immunity.

3.3 Ground (GND)

Ground is the device return pin. The ground pin should have a low impedance connection to the bias supply source return. High peak currents will flow out the ground pin when the capacitive load is being discharged.

3.4 CMOS Push-Pull Output (OUTPUT)

The output is a CMOS push-pull output that is capable of sourcing peak currents of 6A ($V_{DD} = 18V$). The low output impedance ensures the gate of the external MOSFET will stay in the intended state even during large transients. The output pins also have reverse current latch-up ratings of 1.5A.

3.5 Exposed Metal Pad

The exposed metal pad of the DFN package is not internally connected to any potential. Therefore, this pad can be connected to a ground plane or other copper plane on a printed circuit board to aid in heat removal from the package.

3.6 TO-220 Metal Tab

The metal tab on the TO-220 package is at V_{DD} potential. This metal tab is not intended to be the V_{DD} connection to MCP1406/07. V_{DD} should be supplied using the Supply Input pin of the TO-220.

4.0 APPLICATION INFORMATION

4.1 General Information

MOSFET drivers are high-speed, high current devices which are intended to provide high peak currents to charge the gate capacitance of external MOSFETs or IGBTs. In high frequency switching power supplies, the PWM controller may not have the drive capability to directly drive the power MOSFET. A MOSFET driver like the MCP1406/07 family can be used to provide additional drive current capability.

4.2 MOSFET Driver Timing

The ability of a MOSFET driver to transition from a fully-off state to a fully-on state are characterized by the drivers' rise time (t_R), fall time (t_F), and propagation delays (t_{D1} and t_{D2}). The MCP1406/07 family of devices is able to make this transition very quickly. Figure 4-1 and Figure 4-2 show the test circuits and timing waveforms used to verify the MCP1406/07 timing.

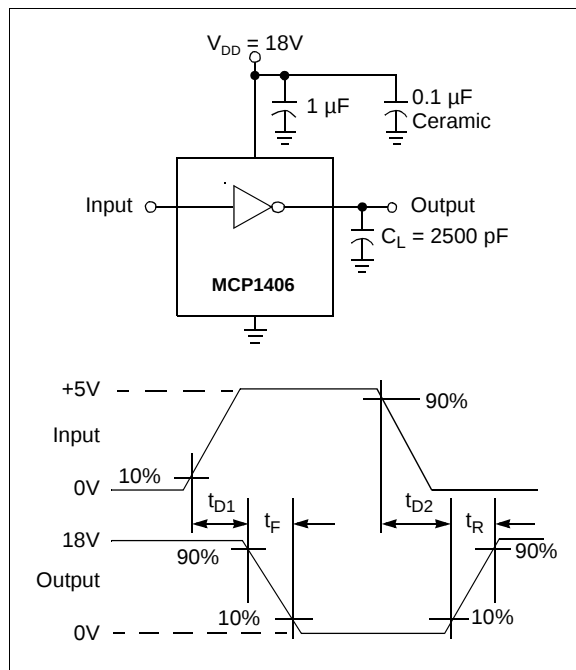


FIGURE 4-1: Inverting Driver Timing Waveform.

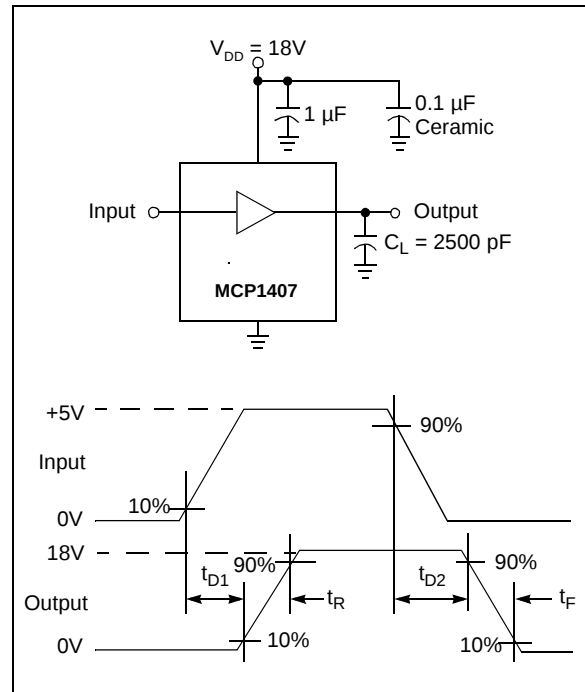


FIGURE 4-2: Non-Inverting Driver Timing Waveform.

4.3 Decoupling Capacitors

Careful layout and decoupling capacitors are highly recommended when using MOSFET drivers. Large currents are required to charge and discharge capacitive loads quickly. For example, 2.25A are needed to charge a 2500 pF load with 18V in 20 ns.

To operate the MOSFET driver over a wide frequency range with low supply impedance, a ceramic and a low ESR film capacitor are recommended to be placed in parallel between the driver V_{DD} and GND. A 1.0 μ F low ESR film capacitor and a 0.1 μ F ceramic capacitor placed between pins 1, 8 and 4, 5 should be used. These capacitors should be placed close to the driver to minimized circuit board parasitics and provide a local source for the required current.

4.4 PCB Layout Considerations

Proper PCB layout is important in a high current, fast switching circuit to provide proper device operation and robustness of design. PCB trace loop area and inductance should be minimized by the use of a ground plane or ground trace located under the MOSFET gate drive signals, separate analog and power grounds, and local driver decoupling.

The MCP1406/07 devices have two pins each for V_{DD} , OUTPUT, and GND. Both pins must be used for proper operation. This also lowers path inductance which will, along with proper decoupling, help minimize ringing in the circuit.

Placing a ground plane beneath the MCP1406/07 will help as a radiated noise shield as well as providing some heat sinking for power dissipated within the device.

4.5 Power Dissipation

The total internal power dissipation in a MOSFET driver is the summation of three separate power dissipation elements.

$$P_T = P_L + P_Q + P_{CC}$$

Where:

P_T = Total power dissipation

P_L = Load power dissipation

P_Q = Quiescent power dissipation

P_{CC} = Operating power dissipation

4.5.1 CAPACITIVE LOAD DISSIPATION

The power dissipation caused by a capacitive load is a direct function of frequency, total capacitive load, and supply voltage. The power lost in the MOSFET driver for a complete charging and discharging cycle of a MOSFET is:

$$P_L = f \times C_T \times V_{DD}^2$$

Where:

f = Switching frequency

C_T = Total load capacitance

V_{DD} = MOSFET driver supply voltage

4.5.2 QUIESCENT POWER DISSIPATION

The power dissipation associated with the quiescent current draw depends upon the state of the input pin. The MCP1406/07 devices have a quiescent current draw when the input is high of 0.13 mA (typ) and 0.035 mA (typ) when the input is low. The quiescent power dissipation is:

$$P_Q = (I_{QH} \times D + I_{QL} \times (1 - D)) \times V_{DD}$$

Where:

I_{QH} = Quiescent current in the high state

D = Duty cycle

I_{QL} = Quiescent current in the low state

V_{DD} = MOSFET driver supply voltage

4.5.3 OPERATING POWER DISSIPATION

The operating power dissipation occurs each time the MOSFET driver output transitions; because, for a very short period of time both MOSFETs in the output stage are on simultaneously. This cross-conduction current leads to a power dissipation, as described by the following equation:

$$P_{CC} = CC \times f \times V_{DD}$$

Where:

CC = Cross-conduction constant (A*sec)

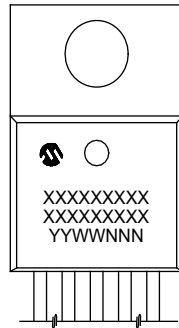
f = Switching frequency

V_{DD} = MOSFET driver supply voltage

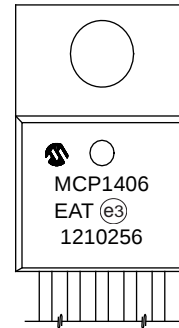
5.0 PACKAGING INFORMATION

5.1 Package Marking Information (Not to Scale)

5-Lead TO-220



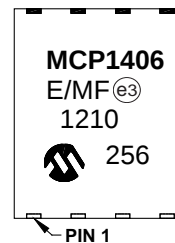
Example



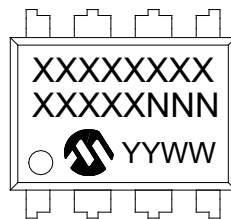
8-Lead DFN-S (6x5x0.9 mm)



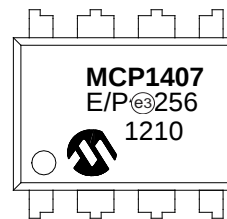
Example



8-Lead PDIP (300 mil)



Example



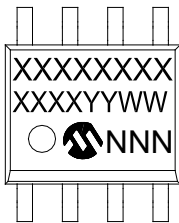
Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	^(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (^(e3)) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

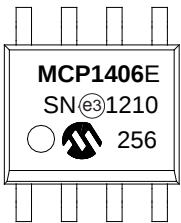
MCP1406/07

5.1 Package Marking Information (Continued)

8-Lead SOIC (3.90 mm)



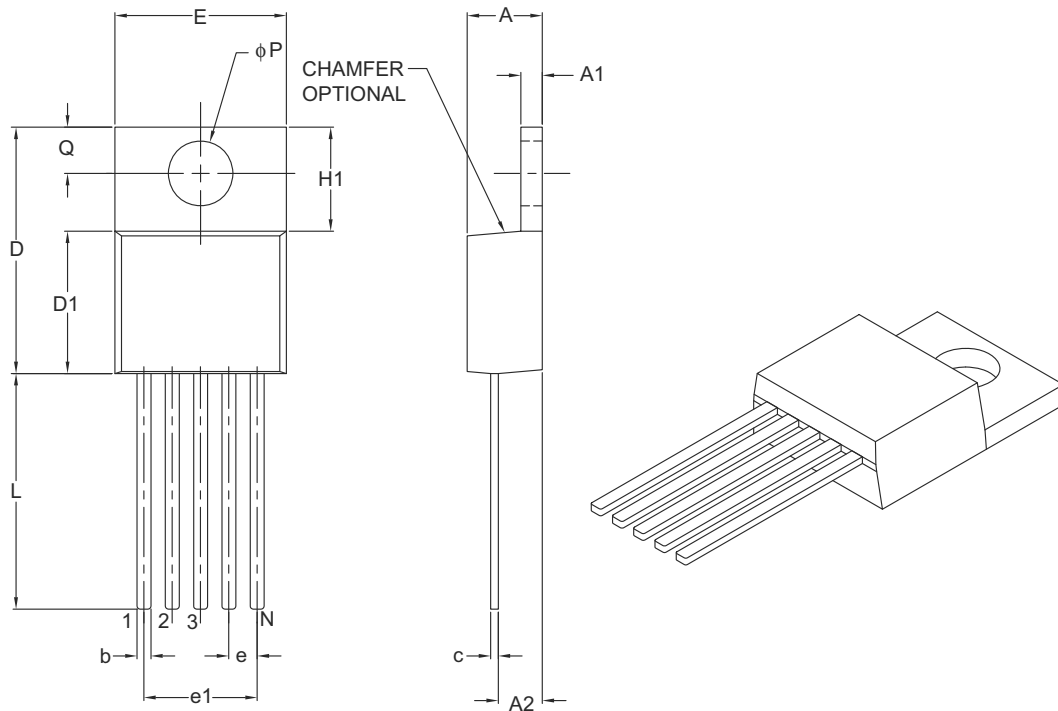
Example



Legend:	XX...X	Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	(e3)	Pb-free JEDEC designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
Note:	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.	

5-Lead Plastic Transistor Outline (AT) [TO-220]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	INCHES		
		MIN	NOM	MAX
Number of Pins	N	5		
Pitch	e	.067 BSC		
Overall Pin Pitch	e1	.268 BSC		
Overall Height	A	.140	—	.190
Overall Width	E	.380	—	.420
Overall Length	D	.560	—	.650
Molded Package Length	D1	.330	—	.355
Tab Length	H1	.204	—	.293
Tab Thickness	A1	.020	—	.055
Mounting Hole Center	Q	.100	—	.120
Mounting Hole Diameter	ϕP	.139	—	.156
Lead Length	L	.482	—	.590
Base to Bottom of Lead	A2	.080	—	.115
Lead Thickness	c	.012	—	.025
Lead Width	b	.015	.027	.040

Notes:

- Dimensions D and E do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .005" per side.
- Dimensioning and tolerancing per ASME Y14.5M.

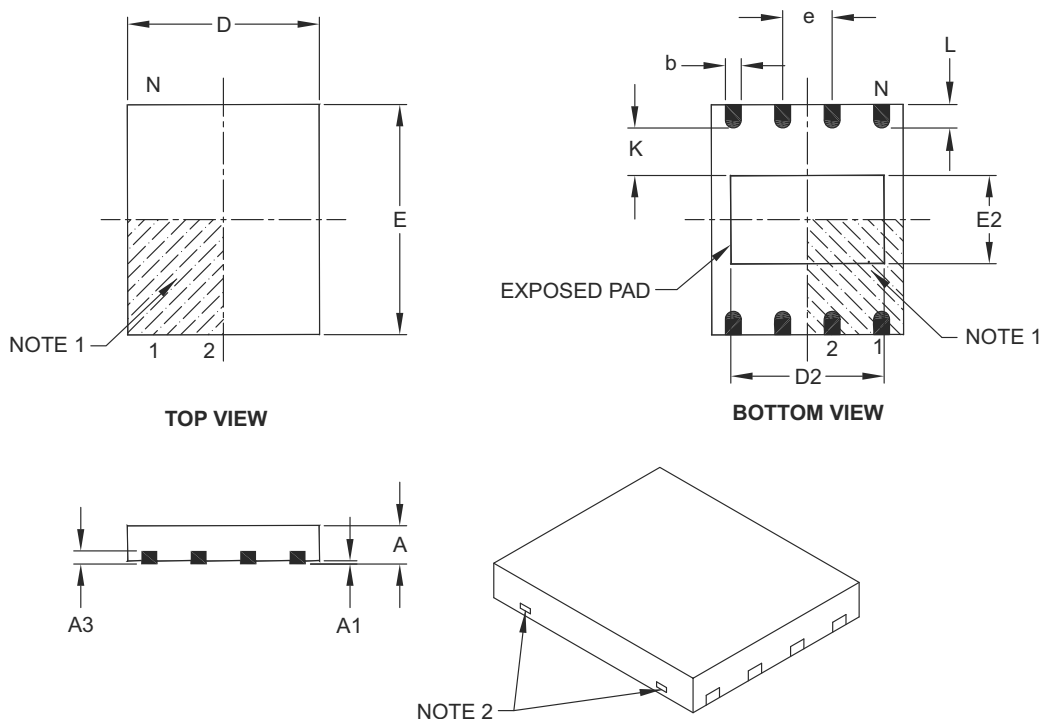
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-036B

MCP1406/07

8-Lead Plastic Dual Flat, No Lead Package (MF) – 6x5 mm Body [DFN-S]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	1.27 BSC		
Overall Height	A	0.80	0.85	1.00
Standoff	A1	0.00	0.01	0.05
Contact Thickness	A3	0.20 REF		
Overall Length	D	5.00 BSC		
Overall Width	E	6.00 BSC		
Exposed Pad Length	D2	3.90	4.00	4.10
Exposed Pad Width	E2	2.20	2.30	2.40
Contact Width	b	0.35	0.40	0.48
Contact Length	L	0.50	0.60	0.75
Contact-to-Exposed Pad	K	0.20	—	—

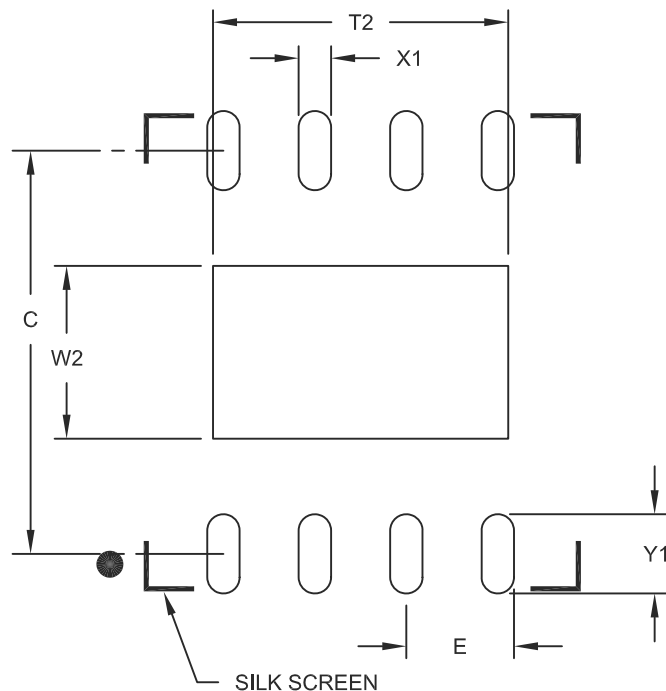
Notes:

- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Package may have one or more exposed tie bars at ends.
- Package is saw singulated.
- Dimensioning and tolerancing per ASME Y14.5M.
BSC: Basic Dimension. Theoretically exact value shown without tolerances.
REF: Reference Dimension, usually without tolerance, for information purposes only.

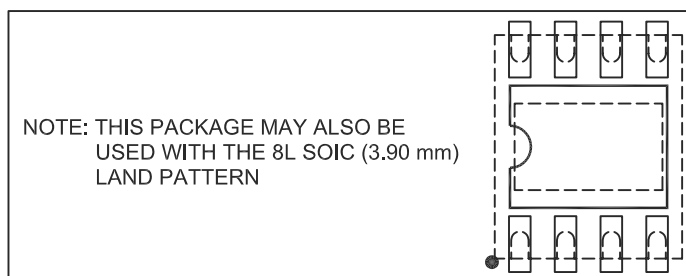
Microchip Technology Drawing C04-122B

8-Lead Plastic Dual Flat, No Lead Package (MF) - 6x5 mm Body [DFN-S]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E	1.27 BSC		
Optional Center Pad Width	W2			2.40
Optional Center Pad Length	T2			4.10
Contact Pad Spacing	C		5.60	
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.10

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

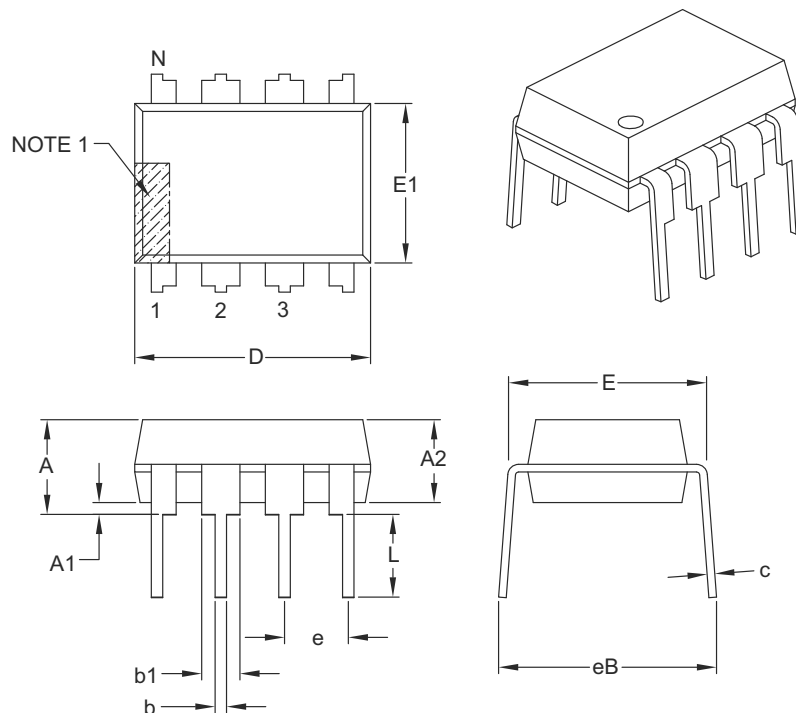
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2122A

MCP1406/07

8-Lead Plastic Dual In-Line (PA) – 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Units		INCHES		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N	8		
Pitch	e	.100 BSC		
Top to Seating Plane	A	–	–	.210
Molded Package Thickness	A2	.115	.130	.195
Base to Seating Plane	A1	.015	–	–
Shoulder to Shoulder Width	E	.290	.310	.325
Molded Package Width	E1	.240	.250	.280
Overall Length	D	.348	.365	.400
Tip to Seating Plane	L	.115	.130	.150
Lead Thickness	c	.008	.010	.015
Upper Lead Width	b1	.040	.060	.070
Lower Lead Width	b	.014	.018	.022
Overall Row Spacing §	eB	–	–	.430

Notes:

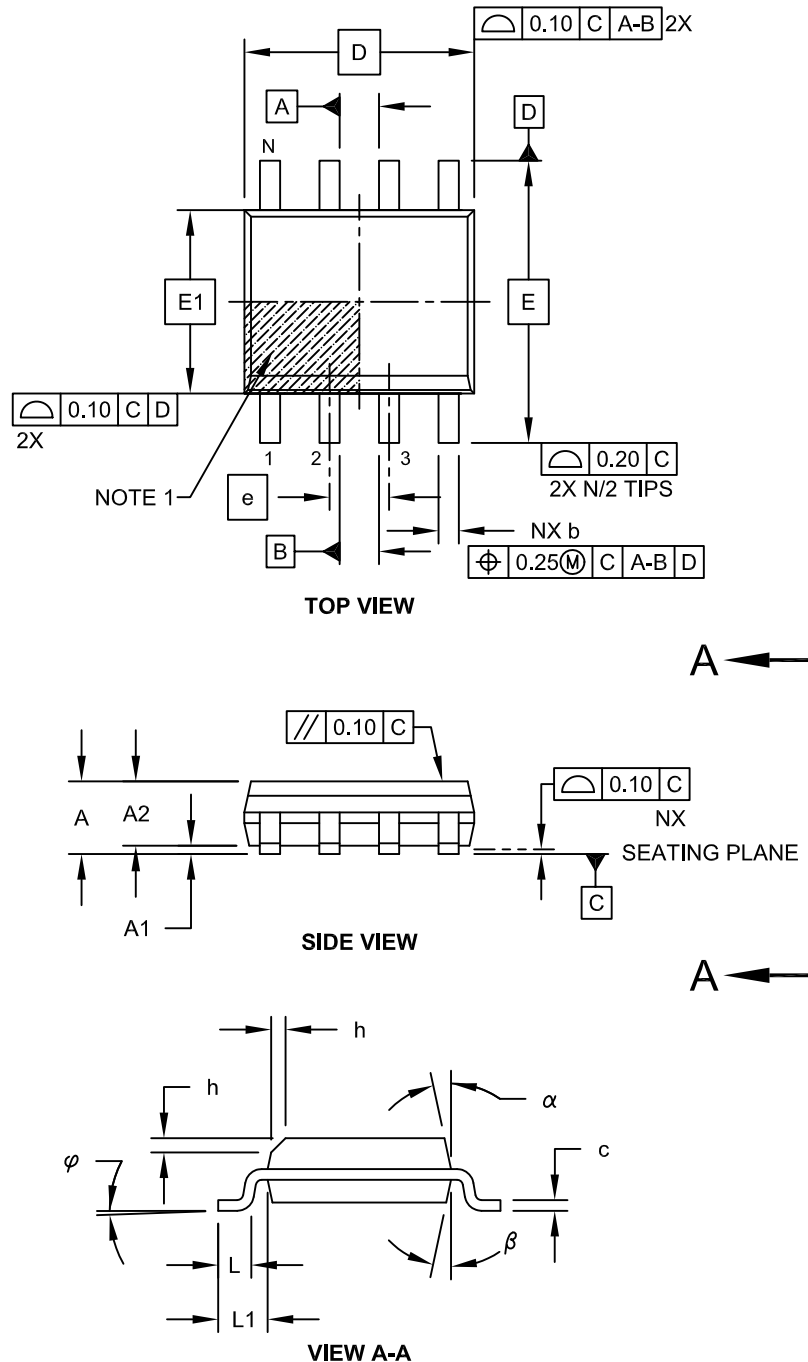
- Pin 1 visual index feature may vary, but must be located with the hatched area.
- § Significant Characteristic.
- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-018B

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>

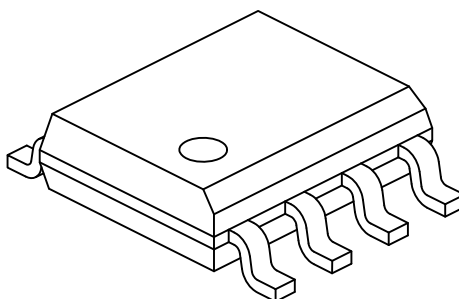


Microchip Technology Drawing No. C04-057C Sheet 1 of 2

MCP1406/07

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



		Units	MILLIMETERS		
Dimension Limits			MIN	NOM	MAX
Number of Pins	N		8		
Pitch	e		1.27 BSC		
Overall Height	A		-	-	1.75
Molded Package Thickness	A2		1.25	-	-
Standoff §	A1		0.10	-	0.25
Overall Width	E		6.00 BSC		
Molded Package Width	E1		3.90 BSC		
Overall Length	D		4.90 BSC		
Chamfer (Optional)	h		0.25	-	0.50
Foot Length	L		0.40	-	1.27
Footprint	L1		1.04 REF		
Foot Angle	φ		0°	-	8°
Lead Thickness	c		0.17	-	0.25
Lead Width	b		0.31	-	0.51
Mold Draft Angle Top	α		5°	-	15°
Mold Draft Angle Bottom	β		5°	-	15°

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. § Significant Characteristic
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
4. Dimensioning and tolerancing per ASME Y14.5M

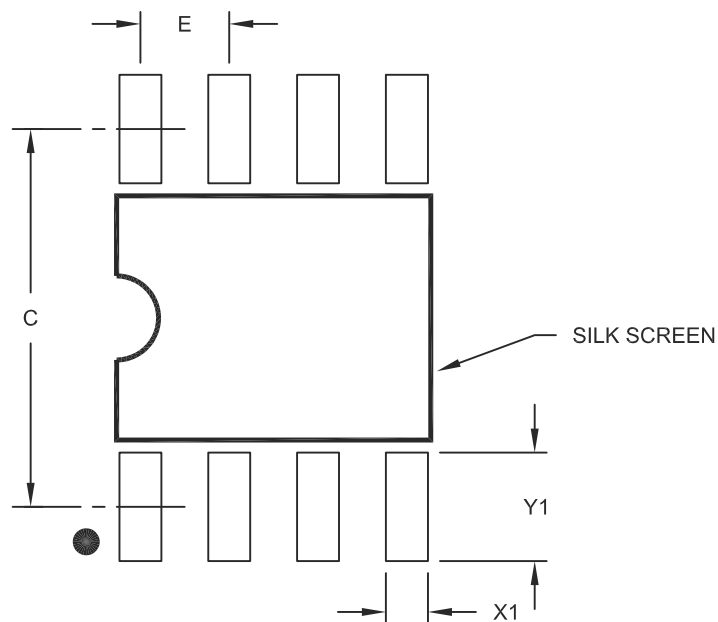
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E	1.27 BSC		
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

NOTES:

APPENDIX A: REVISION HISTORY

Revision B (May 2012)

The following is the list of modifications:

Removed the information referring to the Electrostatic Discharge from the General Description section.

Revision A (December 2006)

Original release of this document.

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO.</u>	<u>X</u>	<u>XX</u>	<u>XXX</u>
Device	Temperature Range	Package	Tape & Reel
Device: MCP1406: 6A High-Speed MOSFET Driver, Inverting MCP1406T: 6A High-Speed MOSFET Driver, Inverting (Tape and Reel) MCP1407: 6A High-Speed MOSFET Driver, Non-Inverting MCP1407T: 6A High-Speed MOSFET Driver, Non-Inverting (Tape and Reel) Temperature Range: E = -40°C to +125°C Package: * AT = TO-220, 5-Lead MF = Dual, Flat, No-Lead (6x5 mm Body), 8-lead PA = Plastic DIP, (300 mil body), 8-lead SN = Plastic SOIC (150 mil Body), 8-Lead * All package offerings are Pb Free (Lead Free)			
Examples: a) MCP1406-E/MF: 6A High-Speed MOSFET Driver, Inverting 8LD DFN package. b) MCP1406-E/AT: 6A High-Speed MOSFET Driver, Inverting 5LD TO-220 package. c) MCP1406-E/SN: 6A High-Speed MOSFET Driver, Inverting 8LD SOIC package. d) MCP1406-E/P: 6A High-Speed MOSFET Driver, Inverting 8LD PDIP package. e) MCP1406T-E/MF: Tape and Reel, 6A High-Speed MOSFET Driver, Inverting, 8LD DFN pkg. f) MCP1406T-E/SN: Tape and Reel, 6A High-Speed MOSFET Driver, Inverting, 8LD SOIC pkg. a) MCP1407-E/MF: 6A High-Speed MOSFET Driver, Non-Inverting 8LD DFN package. b) MCP1407-E/AT: 6A High-Speed MOSFET Driver, Non-Inverting 5LD TO-220 package. c) MCP1407-E/SN: 6A High-Speed MOSFET Driver, Non-Inverting 8LD SOIC package. d) MCP1407-E/P: 6A High-Speed MOSFET Driver, Non-Inverting 8LD PDIP package. e) MCP1407T-E/MF: Tape and Reel, 6A High-Speed MOSFET Driver, Non-Inverting, 8LD DFN pkg. f) MCP1407T-E/SN: Tape and Reel, 6A High-Speed MOSFET Driver, Non-Inverting, 8LD SOIC pkg.			

NOTES:

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- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

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